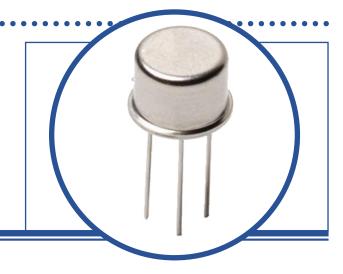
## SILICON PLANAR EPITAXIAL To electronics PNP TRANSISTOR



## 2N2905A

- Hermetic TO-39 Metal package.
- High Speed Saturated Switching
- Screening Options Available

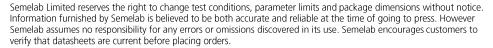


### **ABSOLUTE MAXIMUM RATINGS** (T<sub>A</sub> = 25°C unless otherwise stated)

VCBO	Collector – Base Voltage	-60V		
$V_{CEO}$	Collector – Emitter Voltage	-60V		
$V_{EBO}$	Emitter – Base Voltage	-5V		
IC	Continuous Collector Current	-600mA		
$P_{D}$	Total Power Dissipation at	$T_C = 25^{\circ}C$	3.0W	
		Derate Above 25°C	22.2mW/°C	
$P_{D}$	Total Power Dissipation at	$T_A = 25^{\circ}C$	0.8W	
		Derate Above 25°C	5.9mW/°C	
Tj	Junction Temperature Range	-65 to +200°C		
$T_{stg}$	Storage Temperature Range		-65 to +200°C	

#### THERMAL PROPERTIES

Symbols	Parameters	Мах.	Units
R <sub><b>0</b>JA</sub>	Thermal Resistance, Junction To Ambient	195	°C/W
R <sub><b>0</b>JC</sub>	Thermal Resistance, Junction To Case	50	°C/W





# SILICON PLANAR EPITAXIAL PNP TRANSISTOR 2N2905A



### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise stated)

Symbols	Parameters	Test Conditions		Min.	Тур	Max.	Units	
I <sub>CES</sub>	Collector to emitter Cut-off current	V <sub>CE</sub> = -60V				-1.0		
I <sub>CBO</sub>	Collector Cut-Off Current		$V_{CB} = -60V$			-10	-10	
		T <sub>A</sub> = +150°C	V <sub>CB</sub> = -50V			-10	- μΑ	
I <sub>EBO</sub>	Emitter Cut-Off Current		V <sub>EB</sub> = -5.0V			-10		
			V <sub>EB</sub> = -3.5V			-50	nA	
h <sub>FE</sub> <sup>(1)</sup>	Forward-current transfer ratio		$I_{C} = -0.1 \text{mA}$	75				
			$I_{C} = -1.0 \text{mA}$	100		450		
		V <sub>CE</sub> = -10V	I <sub>C</sub> = -10mA	100				
			$I_{C} = -150 \text{mA}$	100		300		
			I <sub>C</sub> = -500mA	50				
		T <sub>A</sub> = -55°C	I <sub>C</sub> = -1.0mA	50				
V <sub>(BR)</sub> CEO <sup>(1)</sup>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10mA		-60				
V <sub>CE(sat)</sub> <sup>(1)</sup>	Collector-Emitter Saturation Voltage	$I_{C} = -150 \text{mA}$	I <sub>B</sub> = -15mA			-0.4		
		I <sub>C</sub> = -500mA	$I_B = -50 \text{mA}$			-1.6	V	
V <sub>BE(sat)</sub> <sup>(1)</sup>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -150mA	I <sub>B</sub> = -15mA			-1.3		
		I <sub>C</sub> = -500mA	$I_B = -50 \text{mA}$			-2.6		

#### **DYNAMIC CHARACTERISTICS**

t <sub>on</sub>	Turn-on time	$V_{CC} = -30V$ $I_{B1} = -15mA$	I <sub>C</sub> = -150mA		45	ns
toff	Turn-off time	$V_{CC} = -6V$ $I_{B1} = -15\text{mA}$	I <sub>C</sub> = -150mA		300	ns
C <sub>obo</sub>	Output Capacitance	$V_{CB} = -10V$ f = 1.0MHz	I <sub>E</sub> = 0		8	ωĽ
C <sub>ibo</sub>	Input Capacitance	$V_{EB} = -10V$ f = 1.0MHz	I <sub>C</sub> = 0		30	pF
h <sub>fe</sub>	Small Signal Current Gain	$V_{CE} = -20V$ f = 100MHz	I <sub>C</sub> = -50mA	2.0		
h <sub>fe</sub>	Small-signal short-circuit forward-current transfer ratio	$V_{CE} = -10V$ f = 1.0kHz	I <sub>C</sub> = -1.0mA	100		

#### Notes

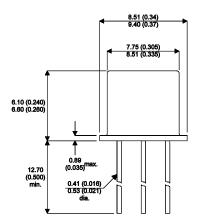
(1) Pulse Width  $\leq$  300us,  $\delta \leq$  2%

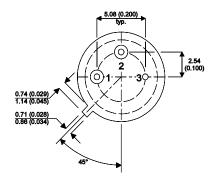
# SILICON PLANAR EPITAXIAL PNP TRANSISTOR 2N2905A



#### **MECHANICAL DATA**

Dimensions in mm (inches)





### TO-39 (TO-205AD) METAL PACKAGE **Underside View**

Pin 1 - Emitter

Pin 2 - Base

Pin 3 - Collector

## **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

TT Electronics: 2N2905A